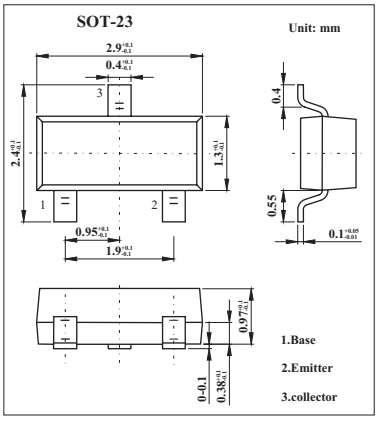
High Performance Transistor

FMMT455



Features

- 140 Volt V_{CEO}
- 1 Amp continuous current
- P_{tot} = 500 mW

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	160	V
Collector-emitter voltage	V_{CEO}	140	V
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CM}	2	A
Collector current	I_C	1	A
Base current	I_B	200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA	160			V
Collector-emitter sustaining voltage *	$V_{CEO(sus)}$	I_C=10mA	140			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA	5			V
Collector cutoff current	I_{CBO}	V_{CB}=140V			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V			0.1	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=150mA,I_B=15mA			0.7	V
Static Forward Current Transfer Ratio	h_{FE}	I_C=150mA,V_{CE}=10V *	100		300	
		I_C=1A, V_{CE}=10V*		10		
Transition frequency	f_T	I_C=50mA,V_{CE}=10V,f=100MHz	100			MHz
Output capacitance	C_{obo}	V_{CB}=10V, I_E=0, f=1MHz			15	pF

* Pulse test: tp = 300 μs; d ⩽ 0.02.

Marking

Marking	455